



Honeywell's Docket No. 30-4790 (4780)
Practitioner's Docket No. 595.48-US1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
WASHINGTON, D.C. 20231

Inventor: **Zhang et al.**

Serial No: **09/357234**

Filed: **July 19, 1999**

For: **Comp. for Chemical Mechanical
Planarization of Copper,
Tantalum and Tantalum Nitride**

Examiner: Brown, Charlotte A.

Art Unit: 1765

RECEIVED
JUN - 5 2001
TC 1700 MAIL ROOM

RESPONSE TO OFFICE ACTION

The Honorable Commissioner
of Patents and Trademarks
Washington, D.C. 20231

Dear Sir:

This paper responds to the Office Action dated November 30, 2000.

IN THE CLAIMS

Please cancel claims 2-11 and enter the following:

1. (Amended) [An etching solution for chemical mechanical planarization of a Cu/Ta/TaN surface] In a chemical mechanical planarization system that includes a Cu/Ta/TaN surface, a replacement single-step etching solution comprising:
 - a) an oxidizing reactant selected from the group consisting of H₂O₂, HNO₃ and mixtures thereof; and[,]
 - b) a co-reactant is selected from the group consisting of H₃PO₄, H₂SO₄, HNO₃, oxalic acid, acetic acid, organic acids and mixtures thereof; and,